

SILICON RECTIFIER DICE (continued)

DIE NO. **IC5819**  
LINE SOURCE — DRL754



This die provides performance equal to or better than that of the following device types:

1N5817  
1N5818  
1N5819

Designed for Schottky  
Barrier low-voltage  
high-frequency rectifier  
applications.

Anode

37 mils

37 mils

Backside: Cathode

**METALLIZATION —**

Top\* ..... Cr Ni Au

Back ..... Cr Ni Au

**DIE THICKNESS** ..... 7 ± 2

**BONDING PAD SIZE:**

Anode ..... 30 x 30 mils

**\*BONDING —** Rectifier chips are designed for solder connections on both sides. Conductive epoxy could be substituted. The metallization is wire bondable using thermocompression or ultrasonic techniques, but adjustments in the machine settings may be necessary because of the metallization system.

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ ; Note 1)

Parameter	Test Conditions	Min	Max	Unit
$V_{RRM}/V_R$		40	—	Volts
$V_F$	$I_F = 1.0$ Amp	—	0.60	Volts
$I_R$	$V_R = 40$ Volts	—	1.0	mAdc

- NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .
2. Detailed device characteristics are available from your Motorola sales representative.